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	AB	4,474,975	10/1984	Clemons et al.			
	AC	5,156,881	10/1992	Okano et al.			
	AD	5,182,221	01/1993	Sato			
	AE	5,410,176	04/1995	Liou et al. EV372470687			
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	AH	5,741,740	04/1998	Jang et al.			
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AICS	AJ	02277253A	11/1990	Japan (Hayashide et al.)				
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	AB	5,801,083	09/1998	Yu et al.			
	AC	5,863,827	01/1999	Joyner			
	AD	5,883,006	03/1999	Iba			
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	AB	5,960,299	09/1999	Yew et al.			
	AC	5,972,773	10/1999	Liu et al.			
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	AB	5,604,149	02/1997	Paoli et al.	437	67	
	AC	5,616,513	04/1997	Shepard	438	402	
	AD	5,786,263	07/1998	Perera	438	431	
	AE	5,895,255	04/1999	Tsuchiaki	438	427	
	AF	5,923,073	07/1999	Aoki et al.	257	501	
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AKS	AA	6,090,675	07/2000	Lee et al.	438	301	
	AB	6,171,962	01/2001	Karlsson et al.	438	692	
	AC	6,187,651	02/2001	Oh	438	435	
	AD	6,191,002	02/2001	Koyanagi	438	431	
	AE	6,326,282	12/2001	Park et al.	438	424	
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	AC	2001/0006255 A1	07/2001	Kwon et al.	257	751	
	AD	2001/0006839 A1	07/2001	Yeo	438	435	
	AE	2001/0046753 A1	11/2001	Gonzalez et al.	438	424	
	AF	2002/0004284 A1	01/2002	Chen	438	427	
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			Chemistry and Chemical Biology, Harvard University, May 14, 2002, pp. 1-13.
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	AE	2003/0032281 A1	2/13/2003	Werkhoven et al.			
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AICS	AK		PCT/US2004/021156; Filed 6/30/2004; Search Report.

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